

METHODS OF FORMING AN INTEGRATED CIRCUIT CAPACITOR IN WHICH
A METAL PREPROCESSED LAYER IS FORMED ON AN ELECTRODE
THEREOF

Abstract of the Disclosure

An integrated circuit capacitor is manufactured by forming a lower electrode on a substrate and forming a metal preprocessed layer on the lower electrode using chemical vapor deposition in which a metal precursor is used as a source gas and the metal precursor comprises oxygen. A dielectric layer is then formed on the metal
5 preprocessed layer and an upper electrode is formed on the dielectric layer. The metal preprocessed layer may reduce oxidation of the lower electrode due to oxygen supplied during formation of the dielectric layer.

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